

# NJVMJD253T4G-VF01

## Complementary Silicon Plastic Power Transistors

### DPAK-3 for Surface Mount Applications

Designed for low voltage, low-power, high-gain audio amplifier applications.

#### Features

- High DC Current Gain
- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves (“-1” Suffix)
- Low Collector-Emitter Saturation Voltage
- High Current-Gain – Bandwidth Product
- Annular Construction for Low Leakage
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable\*
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

| Rating   | Symbol         | Value        | Unit                     |
|--|----------------|--------------|--------------------------|
| Collector-Base Voltage   | $V_{CB}$       | 100          | Vdc                      |
| Collector-Emitter Voltage  | $V_{CEO}$      | 100          | Vdc                      |
| Emitter-Base Voltage   | $V_{EB}$       | 7.0          | Vdc                      |
| Collector Current – Continuous   | $I_C$          | 4.0          | Adc                      |
| Collector Current – Peak   | $I_{CM}$       | 8.0          | Adc                      |
| Base Current   | $I_B$          | 1.0          | Adc                      |
| Total Device Dissipation<br>@ $T_C = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$          | $P_D$          | 12.5<br>0.1  | W<br>W/ $^\circ\text{C}$ |
| Total Device Dissipation<br>@ $T_A = 25^\circ\text{C}$ (Note 2)<br>Derate above $25^\circ\text{C}$ | $P_D$          | 1.4<br>0.011 | W<br>W/ $^\circ\text{C}$ |
| Operating and Storage Junction<br>Temperature Range  | $T_J, T_{stg}$ | -65 to +150  | $^\circ\text{C}$         |
| ESD – Human Body Model   | HBM            | 3B           | V                        |
| ESD – Machine Model  | MM             | C            | V                        |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. When surface mounted on minimum pad sizes recommended.

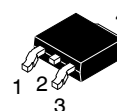
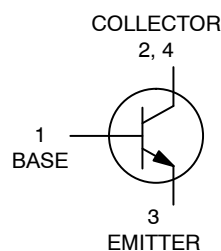


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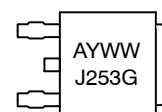
### 4.0 A, 100 V, 12.5 W POWER TRANSISTOR

#### COMPLEMENTARY



DPAK-3  
CASE 369C  
STYLE 1

#### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

#### ORDERING INFORMATION

| Device             | Package           | Shipping†            |
|--------------------|-------------------|----------------------|
| NJVMJD253T4G-VF01* | DPAK<br>(Pb-Free) | 2,500<br>Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NJVMJD253T4G-VF01

## THERMAL CHARACTERISTICS

| Characteristic                         | Symbol          | Value | Unit                 |
|--|-----------------|-------|----------------------|
| Thermal Resistance<br>Junction-to-Case | $R_{\theta JC}$ | 10    | $^{\circ}\text{C/W}$ |
| Junction-to-Ambient (Note 2)           | $R_{\theta JA}$ | 89.3  |                      |

2. When surface mounted on minimum pad sizes recommended.

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^{\circ}\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|----------------|--------|-----|-----|------|
|----------------|--------|-----|-----|------|

### OFF CHARACTERISTICS

|   |               |          |            |                         |
|---|---------------|----------|------------|-------------------------|
| Collector-Emitter Sustaining Voltage (Note 3)<br>( $I_C = 10 \text{ mAdc}$ , $I_B = 0$ )  | $V_{CE(sus)}$ | 100      | -          | Vdc                     |
| Collector Cutoff Current<br>( $V_{CB} = 100 \text{ Vdc}$ , $I_E = 0$ )<br>( $V_{CB} = 100 \text{ Vdc}$ , $I_E = 0$ , $T_J = 125^{\circ}\text{C}$ )                | $I_{CBO}$     | -<br>-   | 100<br>100 | nAdc<br>$\mu\text{Adc}$ |
| Emitter Cutoff Current<br>( $V_{BE} = 7.0 \text{ Vdc}$ , $I_C = 0$ )  | $I_{EBO}$     | -        | 100        | nAdc                    |
| DC Current Gain (Note 3)<br>( $I_C = 200 \text{ mAdc}$ , $V_{CE} = 1.0 \text{ Vdc}$ )<br>( $I_C = 1.0 \text{ Adc}$ , $V_{CE} = 1.0 \text{ Vdc}$ )                 | $h_{FE}$      | 40<br>15 | 180<br>-   | -                       |
| Collector-Emitter Saturation Voltage (Note 3)<br>( $I_C = 500 \text{ mAdc}$ , $I_B = 50 \text{ mAdc}$ )<br>( $I_C = 1.0 \text{ Adc}$ , $I_B = 100 \text{ mAdc}$ ) | $V_{CE(sat)}$ | -<br>-   | 0.3<br>0.6 | Vdc                     |
| Base-Emitter Saturation Voltage (Note 3)<br>( $I_C = 2.0 \text{ Adc}$ , $I_B = 200 \text{ mAdc}$ )  | $V_{BE(sat)}$ | -        | 1.8        | Vdc                     |
| Base-Emitter On Voltage (Note 3)<br>( $I_C = 500 \text{ mAdc}$ , $V_{CE} = 1.0 \text{ Vdc}$ )   | $V_{BE(on)}$  | -        | 1.5        | Vdc                     |

### DYNAMIC CHARACTERISTICS

|   |          |    |    |     |
|---|----------|----|----|-----|
| Current-Gain - Bandwidth Product (Note 4)<br>( $I_C = 100 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f_{test} = 10 \text{ MHz}$ ) | $f_T$    | 40 | -  | MHz |
| Output Capacitance<br>( $V_{CB} = 10 \text{ Vdc}$ , $I_E = 0$ , $f = 0.1 \text{ MHz}$ )   | $C_{ob}$ | -  | 50 | pF  |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\approx$  2%.

4.  $f_T = |h_{FE}| \cdot f_{test}$ .

# NJVMJD253T4G-VF01

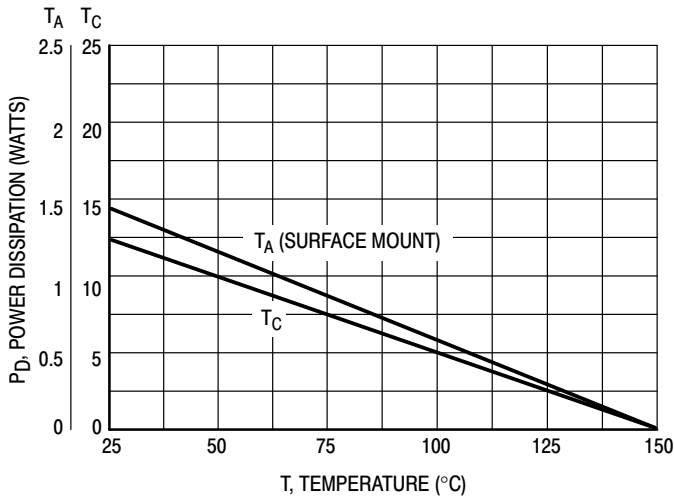


Figure 1. Power Derating

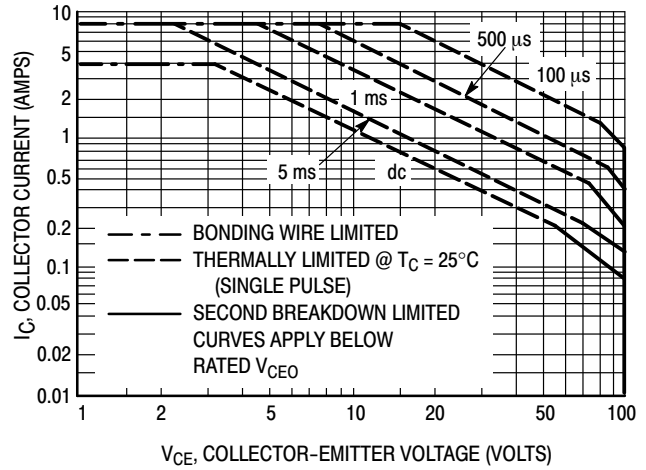


Figure 2. Active Region Maximum Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 3. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

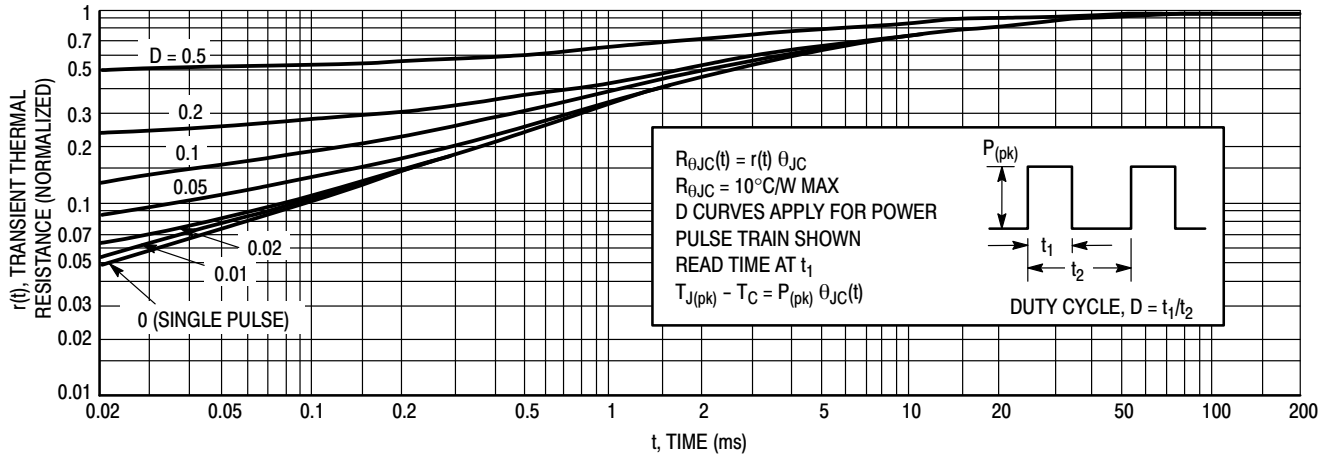


Figure 3. Thermal Response

# NJVMJD253T4G-VF01

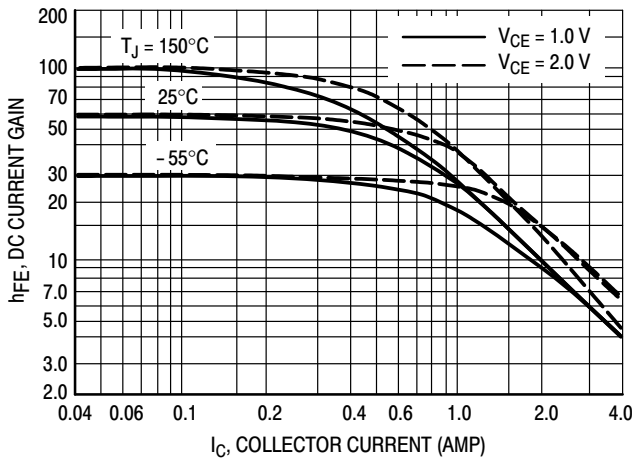


Figure 4. DC Current Gain

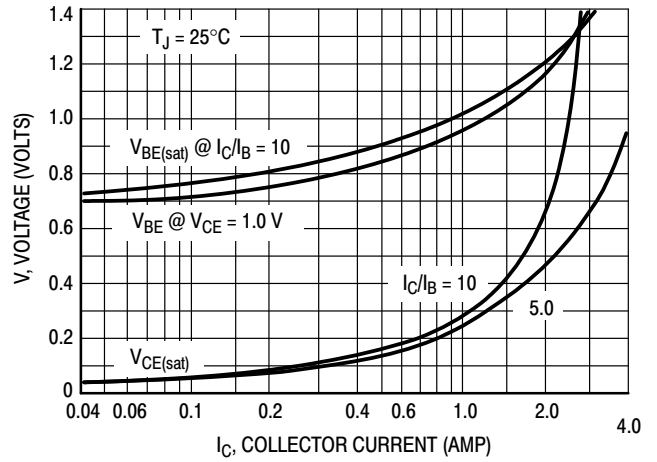


Figure 5. "On" Voltages

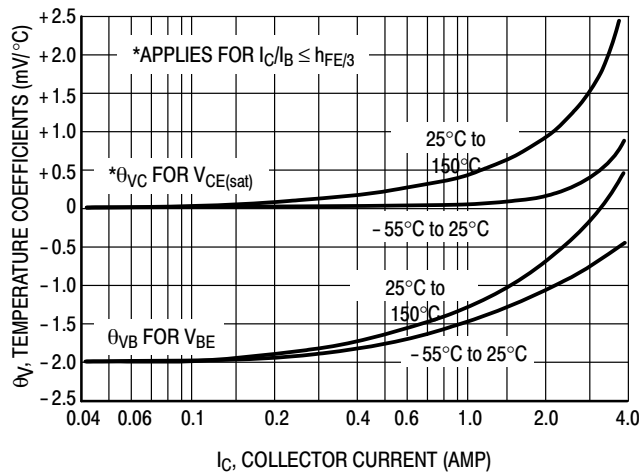
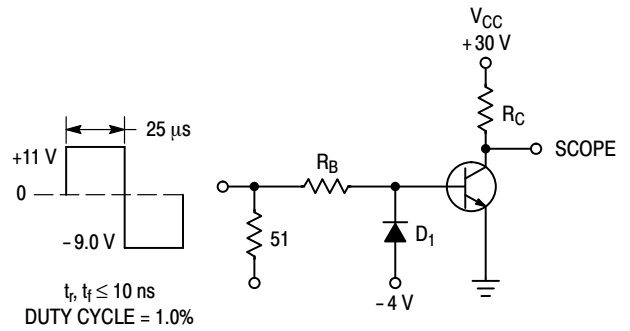


Figure 6. Temperature Coefficients



$R_B$  and  $R_C$  VARIED TO OBTAIN DESIRED CURRENT LEVELS  
 $D_1$  MUST BE FAST RECOVERY TYPE, e.g.:  
 1N5825 USED ABOVE  $I_B \approx 100$  mA  
 MSD6100 USED BELOW  $I_B \approx 100$  mA  
 FOR PNP TEST CIRCUIT, REVERSE ALL POLARITIES

Figure 7. Switching Time Test Circuit

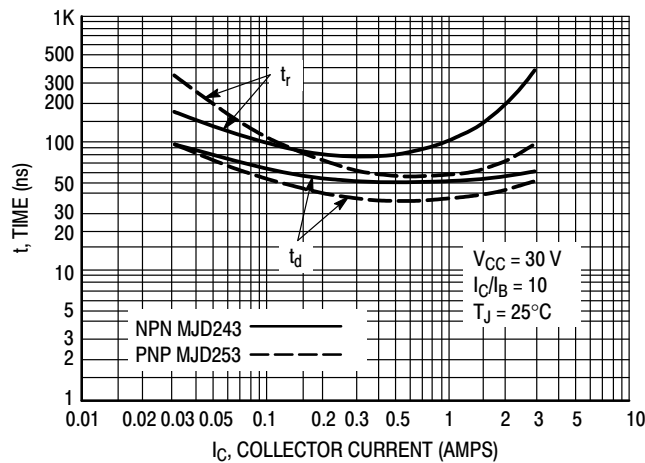


Figure 8. Turn-On Time

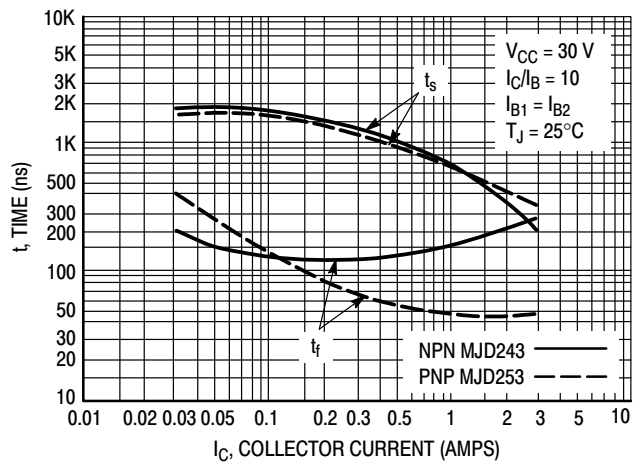


Figure 9. Turn-Off Time

# NJVMJD253T4G-VF01

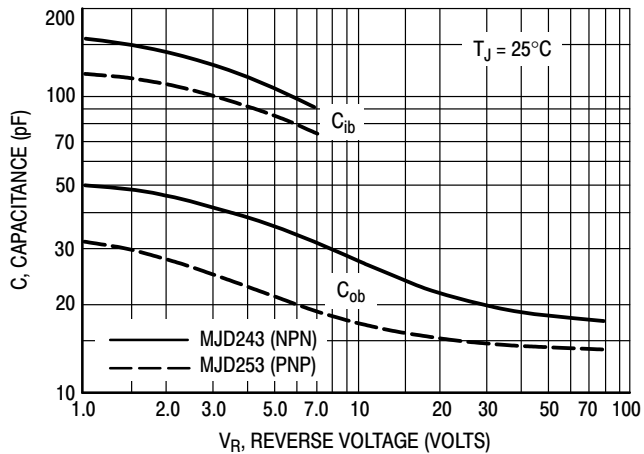


Figure 10. Capacitance

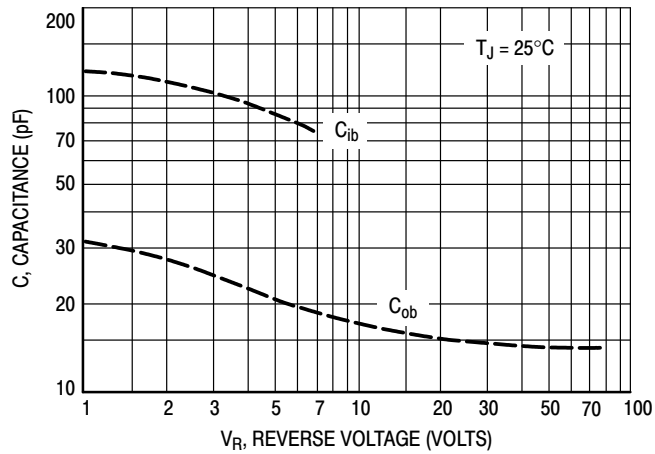
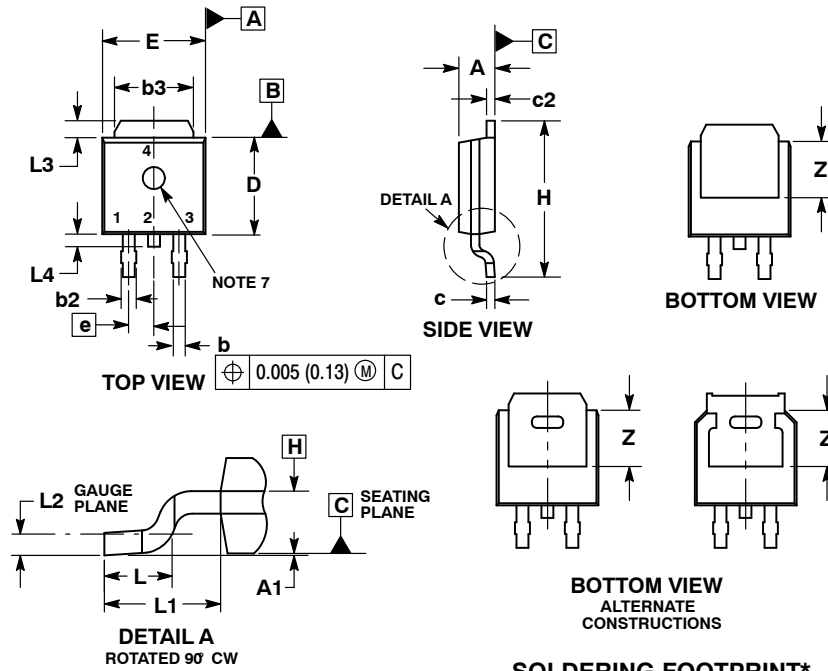


Figure 11. Capacitance

# NJVMJD253T4G-VF01

## PACKAGE DIMENSIONS

### DPAK (SINGLE GAUGE) CASE 369C ISSUE F

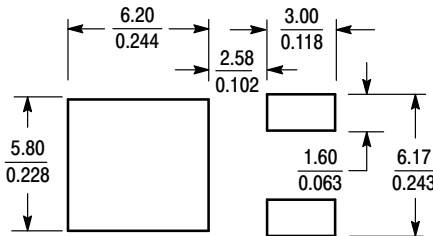


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

| DIM | INCHES    |       | MILLIMETERS |       |
|-----|-----------|-------|-------------|-------|
|     | MIN       | MAX   | MIN         | MAX   |
| A   | 0.086     | 0.094 | 2.18        | 2.38  |
| A1  | 0.000     | 0.005 | 0.00        | 0.13  |
| b   | 0.025     | 0.035 | 0.63        | 0.89  |
| b2  | 0.028     | 0.045 | 0.72        | 1.14  |
| b3  | 0.180     | 0.215 | 4.57        | 5.46  |
| c   | 0.018     | 0.024 | 0.46        | 0.61  |
| c2  | 0.018     | 0.024 | 0.46        | 0.61  |
| D   | 0.235     | 0.245 | 5.97        | 6.22  |
| E   | 0.250     | 0.265 | 6.35        | 6.73  |
| e   | 0.090 BSC |       | 2.29 BSC    |       |
| H   | 0.370     | 0.410 | 9.40        | 10.41 |
| L   | 0.055     | 0.070 | 1.40        | 1.78  |
| L1  | 0.114 REF |       | 2.90 REF    |       |
| L2  | 0.020 BSC |       | 0.51 BSC    |       |
| L3  | 0.035     | 0.050 | 0.89        | 1.27  |
| L4  | ---       | 0.040 | ---         | 1.01  |
| Z   | 0.155     | ---   | 3.93        | ---   |

### SOLDERING FOOTPRINT\*



SCALE 3:1 (mm/inches)

**STYLE 1:**

1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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